

ABSTRACT

5 A semiconductor light emitting device including a transparent compound semiconductor substrate whose lattice constant is inconsistent with the compound semiconductor emitting the light and exhibiting high light output is obtained. A semiconductor light emitting device(10) includes a GaP substrate(1), an active layer(4) located above GaP substrate(1) and including an n-type AlInGaP layer and a p-type AlInGaP layer, and an ELO layer(3) located between GaP substrate(1) and active layer(4) and formed by epitaxial lateral growth.